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current (0.3 μ A max., $V_{DD}=1.5$ V) and has a wide operating voltage range. Data can be read serially by clock pulses from address address 64. All the addresses are initialized at "H" so writing in can be done only once.

■ **Features**

- Low standby current (0.3 μ A max., $V_{DD}=1.5$ V)
- Wide operating voltage range

■ **Applications**

- Pager ID ROM
- Cordless telephone
- Security equipment

■ **Pin Assignment**

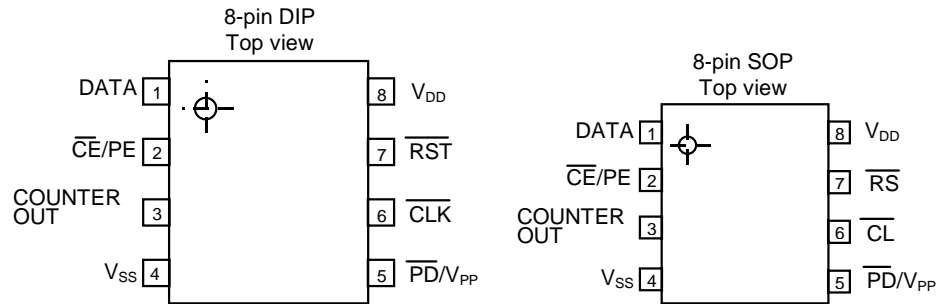


Figure 1

■ **Block Diagram**

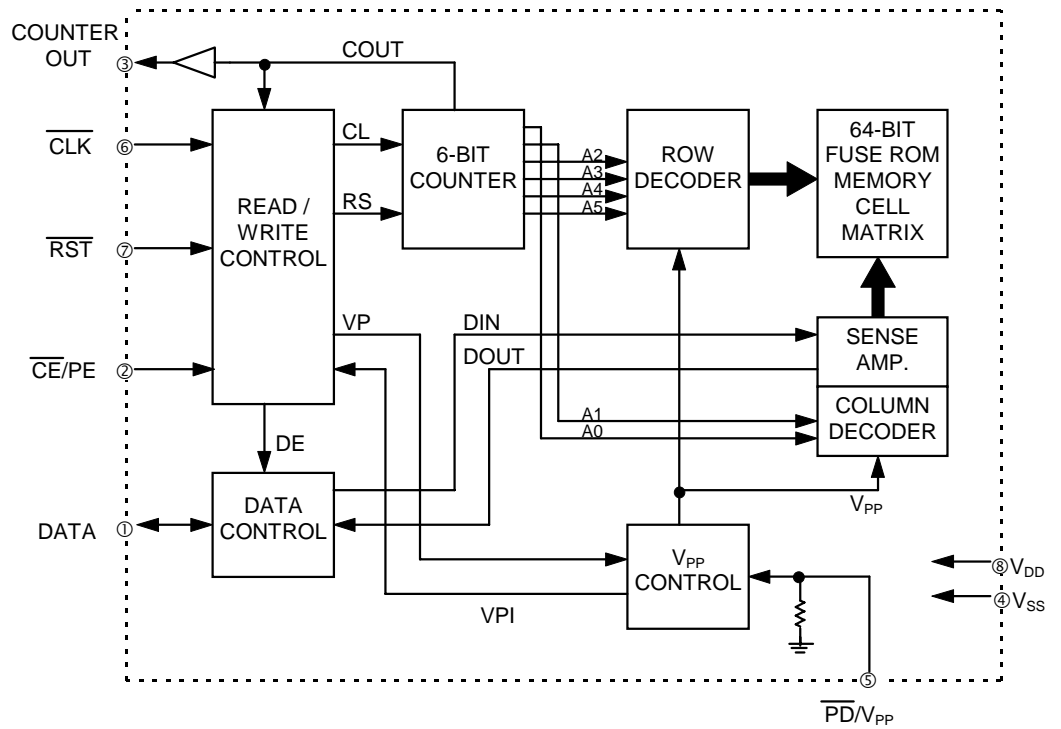


Figure 2

2	CE/PE	Mode select terminal	(Refer to operation mode table)
3	COUNTER OUT	Counter output terminal	6-bit counter; 64th bit detection output terminal
4	V _{SS}	Negative power supply terminal	Normally, connected to GND.
5	$\overline{P_D/V_{PP}}$	Program voltage input terminal	Input terminal of writing voltage to FUSE memory at 21 V. (Refer to operation mode table.) Pull-down resistor built in.
6	\overline{CLK}	Clock input terminal	Clock input terminal of 6-bit counter. Operates at the falling edge.
7	\overline{RST}	Reset input terminal	Reset input terminal of 6-bit counter. Operates at "L".
8	V _{DD}	Positive power supply terminal	Normally, connected to +1.1 to +5.5 V.

■ Mode Table

Table 2

Terminal	$\overline{CE/PE}$	$\overline{P_D/V_{PP}}$	\overline{CLK}	\overline{RST}	DATA
Read	V _{SS}	V _{SS}	Input possible	Input possible	Data output
Counter hold	V _{DD}	V _{SS}	Input impossible	Input impossible	High impedance
Program	V _{DD}	V _{PP}	Input impossible	Input impossible	Data input

■ Absolute Maximum Ratings

Table 3

Parameter	Symbol	Ratings	Unit
Power supply voltage	V _{DD}	-0.3 to +6.5	V
P _D /V _{PP} input voltage	V _{PP}	-0.3 to 26	V
Input voltage	V _{IN}	V _{SS} -0.3 to V _{DD} +0.3	V
Output voltage	V _{OUT}	V _{SS} -0.3 to V _{DD} +0.3	V
Storage temperature under bias	V _{bias}	-30 to +85	°C
Storage temperature	V _{stg}	-40 to +125	°C

■ Recommended Operating Conditions

Table 4

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Power supply voltage	V _{DD}	Ta=25°C, Read, t _{CH} =15μs	1.1	1.5	5.5	V
		Ta=25°C, Write	4.5	5.0	5.5	V
High level input voltage	V _{IH}	Ta=25°C, Read	V _{DD} -0.3	—	V _{DD}	V
		Ta=25°C, Write	V _{DD} -0.3	—	V _{DD}	V
Low level input voltage	V _{IL}	Ta=25°C, Read	-0.3	—	0.3	V
		Ta=25°C, Write	-0.3	—	0.5	V
Operating temperature	V _{opr}		-20	—	70	°C

consumption						
Standby current consumption	I_{DDs}	$V_{DD}=1.5\text{ V}, \overline{RST}=V_{DD}$ $CLK=V_{DD}, \overline{CE/PE}=V_{SS}$	—	—	0.3	μA
$\overline{P_D}/V_{PP}$ input voltage	V_{PP}		20	21	22	V
$\overline{P_D}/V_{PP}$ input current	I_{PP}		—	—	150	mA
Output current	I_{OH}	$V_{DD}=1.1\text{ to }5.5\text{ V}, V_{OH}=V_{DD}-0.3\text{ V}$	-300	—	—	μA
	I_{OL}	$V_{DD}=1.1\text{ to }5.5\text{ V}, V_{OH}=0.3\text{ V}$	300	—	—	μA
Pull-down resistance	R_D	$V_{DD}=1.5\text{ V}$	0.1	0.2	0.4	$M\Omega$

■ AC Electrical Characteristics

1. Read mode

Table 6

($T_a=25^\circ\text{C}, V_{DD}=1.5\text{ V}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit
\overline{RST} hold time	t_{RH}	5.0	—	—	μs
Read cycle time	t_{RC}	2.0	—	—	μs
\overline{CLK} hold time	t_{CH}	5.0	—	—	μs
Access time	t_{ACC}	—	—	5.0	μs
$\overline{CE/PE}$ setup time	t_{CES}	2.0	—	—	μs
\overline{RST} setup time	t_{RS}	5.0	—	—	μs
\overline{CLK} setup time	t_{CS}	5.0	—	—	μs
\overline{CE} access time	t_{CE}	—	—	5.0	μs
Output disable time	t_{WZ}	—	—	500	ns
\overline{CLK} and \overline{RST} inhibit time	t_{CRI}	—	—	500	ns

Load : 60 pF

2. Write mode

Table 7

($T_a=25^\circ\text{C}, V_{DD}=5.0\text{ V}, V_{PP}=21\text{ V}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit
CE-data setup time	t_{CDS}	0.5	—	—	μs
Data setup time	t_{DS}	0.5	—	—	μs
Data hold time	t_{DH}	0	—	—	μs
CE-data hold time	t_{CDH}	2.0	—	—	μs
V_{PP} rise time	t_r	20	—	—	μs
Program pulse width	t_{PW}	8.0	—	—	ms
V_{PP} rise slope	ΔV_{PP}	—	—	4	V/ μs

does not accept any more CLK pulses and the counter does not operate. The data of address 64 is maintained till address 1 is read by the $\overline{\text{RST}}$ pulse.

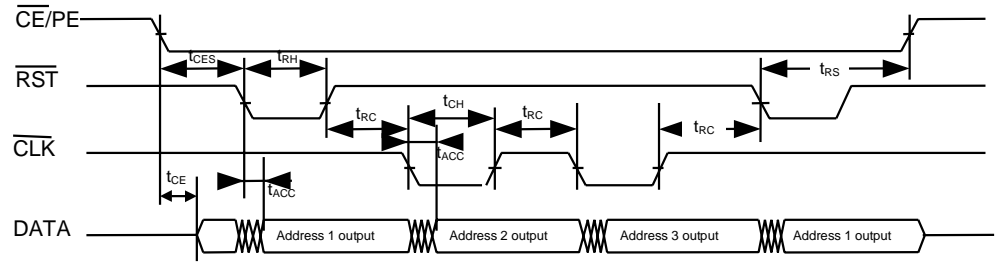


Figure 3 Read mode timing

- *1 When both the $\overline{\text{CLK}}$ and $\overline{\text{RST}}$ terminals are at "H" level.
- *2 When the $\overline{\text{RST}}$ terminal is at "L" level, the latch is transparent and the data is recognized by the rising of the $\overline{\text{RST}}$ pulse.
- *3 Data read by the $\overline{\text{CLK}}$ pulse is latched at its rising.

Counter Hold Mode Operation

By setting the $\overline{\text{CE/PE}}$ terminal to "H" level, the S-2100R enters the counter hold mode and the DATA terminal becomes high impedance. ^{*4}

In counter hold mode, the $\overline{\text{CLK}}$ and $\overline{\text{RST}}$ pulses which fall while the $\overline{\text{CE/PE}}$ terminal is at "H" level are recognized to be invalid and there is no change in counter and data output. When the $\overline{\text{CE/PE}}$ terminal is set to "L" level again, it returns to the condition in which it was before the counter hold mode.

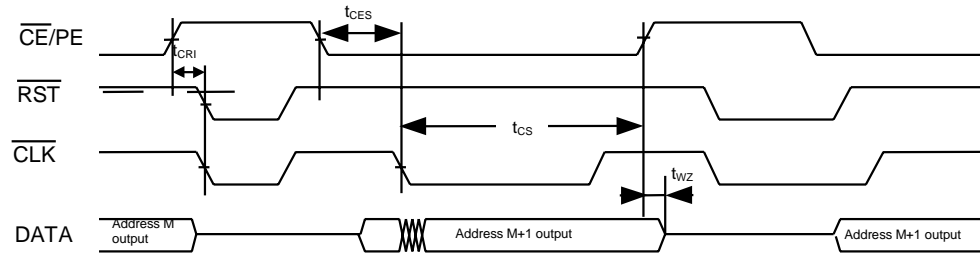


Figure 4 Counter hold mode timing

- *4 When both the CLK and RST terminals are at "H" level.

be written into the selected address only once.

If you continue writing from address 1 to 64, the output of the COUNTER OUT terminal goes to "H" level, just like in the read mode and no more $\overline{\text{CLK}}$ pulses or writing pulses in program mode can be accepted.

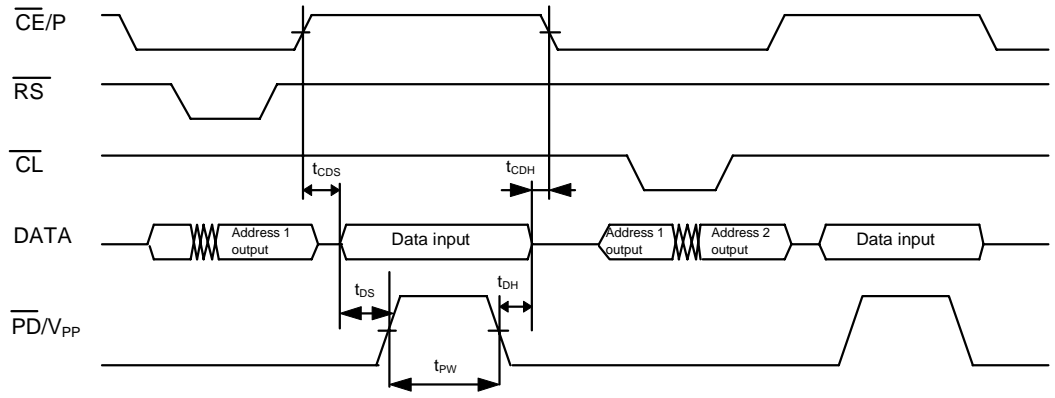


Figure 5 Program mode timing

- *5 In program mode, operate at $V_{\text{DD}}=5.0\text{ V}$ to assure reliability of the data writing.
- *6 The selection of addresses is possible only in read mode. Address 1 is selected by $\overline{\text{RST}}$ pulses and writing proceeds sequentially from address 1 by $\overline{\text{CLK}}$ pulse.
- *7 All the memories are initially at "H" level, so writing into "L" can be done. When data is at "H" level, writing voltage can be supplied to the memory.
- *8 Address 1 is selected again by the $\overline{\text{RST}}$ pulse. The addresses which are not written to "L" level are at "H" level, so writing "L" level in these addresses is possible.

If the $\overline{\text{CLK}}$ and $\overline{\text{RST}}$ pulses which are input in the counter hold mode are still at "L" level after setting the $\overline{\text{CE/PE}}$ terminal to "L" level, these $\overline{\text{CLK}}$ and $\overline{\text{RST}}$ terminals are ignored. The mode shifts to read mode and data which is held before the shift is output at the DATA terminal. *11

In program mode, inputting the DATA terminal before the $\overline{\text{CE/PE}}$ terminal goes to "H" level is prohibited. Also, charging the writing voltage from the P_D/V_{PP} terminal is prohibited when the $\overline{\text{CE/PE}}$ terminal is at "L" level. In program mode, input to the DATA terminal must be decided before charging the writing voltage. *12

*9 Input of the $\overline{\text{CLK}}$ and $\overline{\text{RST}}$ pulses is not recognized as valid unless both pulses are input at "H" level.

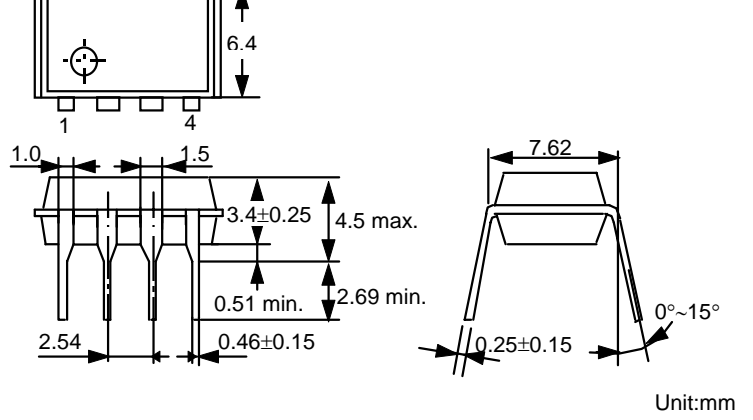
*10 The counter hold mode is entered when reading of the $\overline{\text{CLK}}$ and $\overline{\text{RST}}$ pulses has been finished and DATA output has been stabilized.

*11 No more $\overline{\text{CLK}}$ or $\overline{\text{RST}}$ pulses are accepted unless both the $\overline{\text{CLK}}$ and $\overline{\text{RST}}$ terminals are at "H" level.

*12 If data input is changed while writing voltage is supplied, the S-2100R does not accept the changed data.

■ Notes

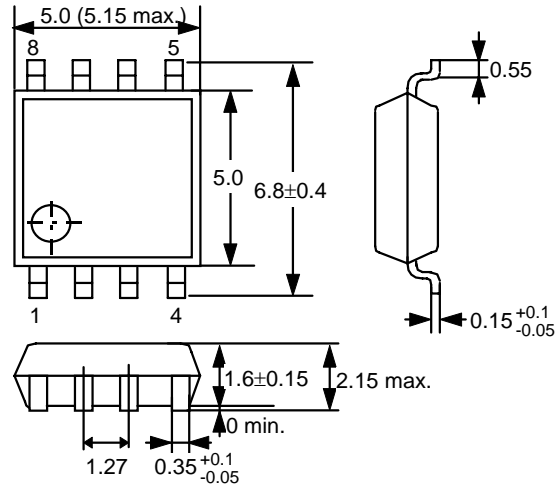
Memory should not be accessed for at least 10 μs after voltage is supplied and goes to V_{DD} .



Unit:mm

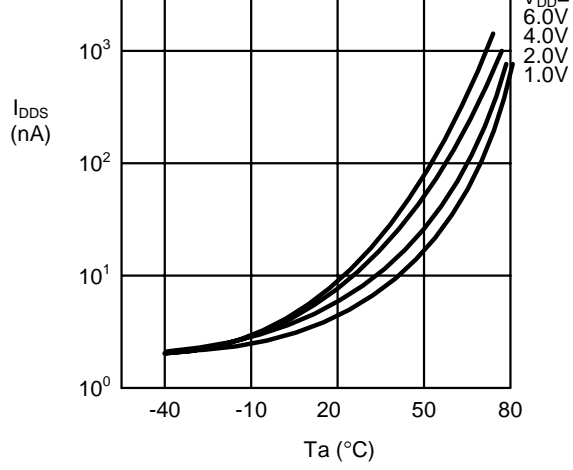
Figure 6

2. 8-pin SOP

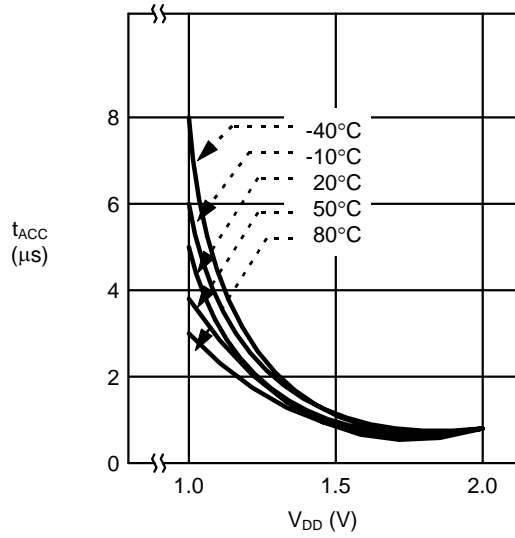


Unit: mm

Figure 7



2. Access time t_{ACC} -
Power supply voltage V_{DD}



3. Access time t_{ACC} -
Power supply voltage V_{DD}

